

Abstract of the Disclosure:

A contact configuration has an ohmic contact between a metalization layer and a semiconductor body of monocrystalline semiconductor material. An amorphous semiconductor layer is
5 formed between the metalization layer and the monocrystalline semiconductor body. The layer is formed of the same semiconductor material as the body. The contact configuration is either produced by applying amorphous semiconductor material on the semiconductor body (e.g., sputtering, vapor
10 deposition, glow discharge) or by damage formation in the semiconductor body.

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